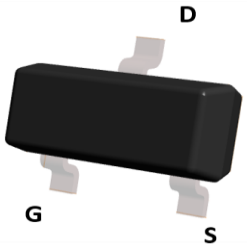
Leading Circuit Protection
Products and Solutions

LXN540C

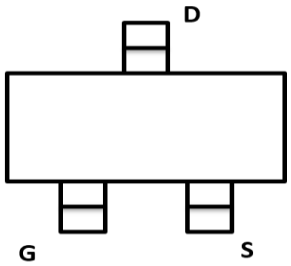
N-Channel Enhancement Mode Field Effect Transistor

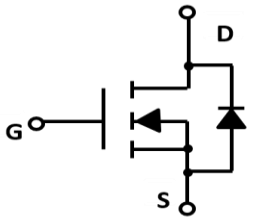
Product Summary

- V_{DS} 40V
- I_D 5A
- $R_{DS(ON)}$(at V_{GS}=10V) ＜45mohm
- $R_{DS(ON)}$(at V_{GS}=4.5V) ＜60mohm



Top View





SOT-23

General Description

- Trench Power LV MOSFET technology
- High Power and current handing capability

Applications

- PWM application
- Load switch

Absolute Maximum Ratings (TA=25℃unless otherwise noted)

Parameter		Symbol	Limit	Unit
Drain-source Voltage		V_{DS}	40	V
Gate-source Voltage		V_{GS}	±20	V
Drain Current	T_A=25℃ @ Steady State	I_D	5	A
	T_A=70℃ @ Steady State		4	
Pulsed Drain Current[A]		I_{DM}	20	A
Total Power Dissipation @ T_A=25℃		P_D	1.2	W
Thermal Resistance Junction-to-Ambient @ Steady State[B]		$R_{\theta JA}$	104	℃/ W
Junction and Storage Temperature Range		T_J ,T_{STG}	-55～+150	℃

Ordering Information (Example)

PREFERED P/N	PACKING CODE	Marking	MINIMUM PACKAGE(pcs)	INNER BOX QUANTITY(pcs)	OUTER CARTON QUANTITY(pcs)	DELIVERY MODE
LXN540C	F2		3000	30000	120000	7“ reel

Electrical Characteristics (T_J=25℃ unless otherwise noted)

Parameter	Symbol	Conditions	Min	Typ	Max	Units
Static Parameter						
Drain-Source Breakdown Voltage	BV_{DSS}	V_{GS}= 0V, I_D=250μA	40			V
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=40V,V_{GS}=0V,T_C=25℃			1	μA
Gate-Body Leakage Current	I_{GSS1}	V_{GS}= ±20V, V_{DS}=0V			±100	nA
	I_{GSS2}	V_{GS}= ±10V, V_{DS}=0V			±50	nA
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS}= V_{GS}, I_D=250μA	1.0	1.5	2.5	V
Static Drain-Source On-Resistance	$R_{DS(ON)}$	V_{GS}= 10V, I_D=5A		30	45	mΩ
		V_{GS}= 4.5V, I_D=3A		40	60	
Diode Forward Voltage	V_{SD}	I_S=5A,V_{GS}=0V			1.2	V
Maximum Body-Diode Continuous Current	I_S				5	A
Dynamic Parameters						
Input Capacitance	C_{iss}	V_{DS}=20V,V_{GS}=0V,f=1MHZ		490		pF
Output Capacitance	C_{oss}			92		
Reverse Transfer Capacitance	C_{rss}			68		
Switching Parameters						
Total Gate Charge	Q_g	V_{GS}=10V,V_{DS}=20V,I_D=3.5A		5.2		nC
Gate Source Charge	Q_{gs}			0.9		
Gate Drain Charge	Q_{gd}			1.3		
Turn-on Delay Time	$t_{D(on)}$	V_{GS}=10V,V_{DD}=20V, R_L=2Ω, R_{GEN}=3Ω		13		ns
Turn-on Rise Time	t_r			52		
Turn-off Delay Time	$t_{D(off)}$			17		
Turn-off Fall Time	t_f			10		

A. Pulse Test: Pulse Width≤300us,Duty cycle ≤2%.
B. Device mounted on FR-4 PCB, 1 inch x 0.85 inch x 0.062 inch.

Typical Performance Characteristics

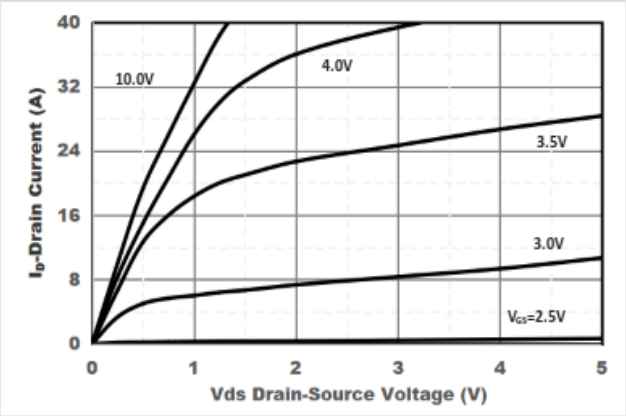


Figure1. Output Characteristics

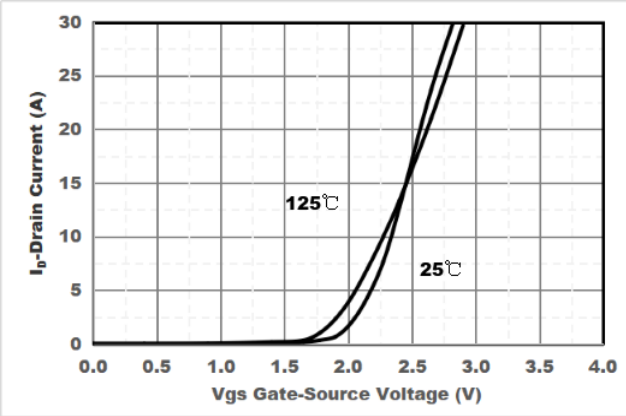


Figure2. Transfer Characteristics

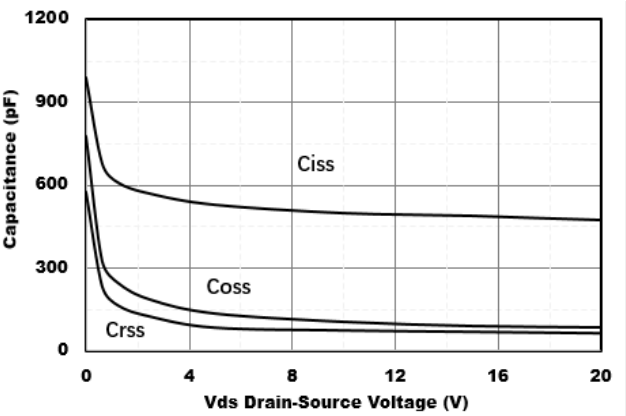


Figure3. Capacitance Characteristics

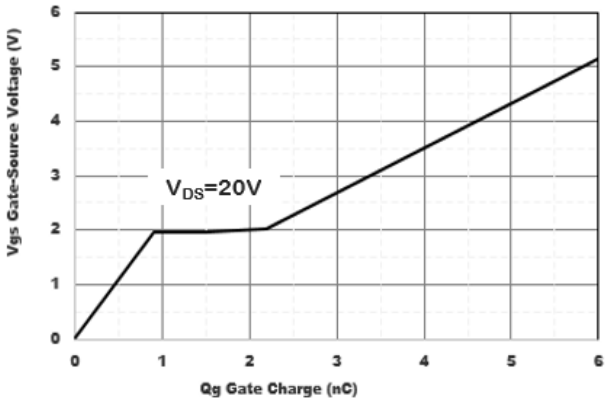


Figure4. Gate Charge

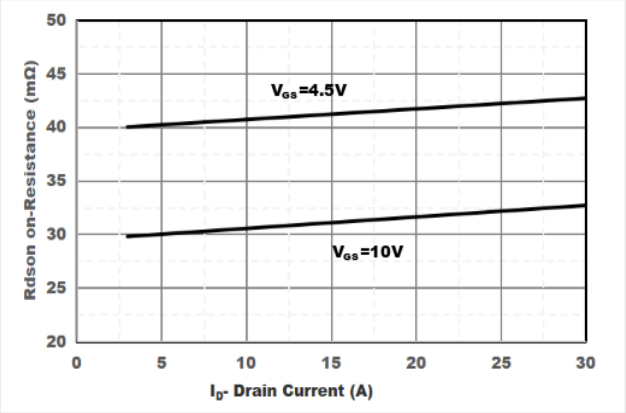


Figure5. Drain-Source on Resistance

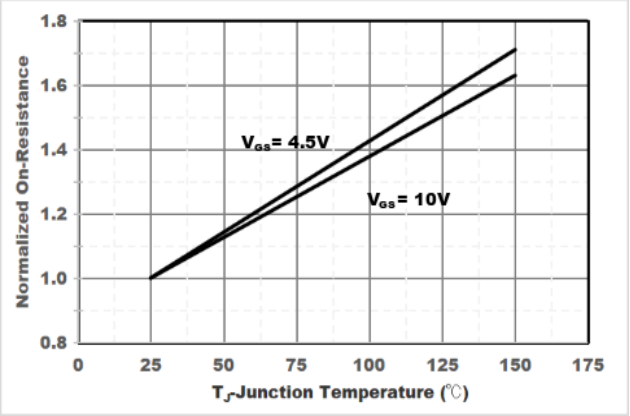


Figure6. Drain-Source on Resistance

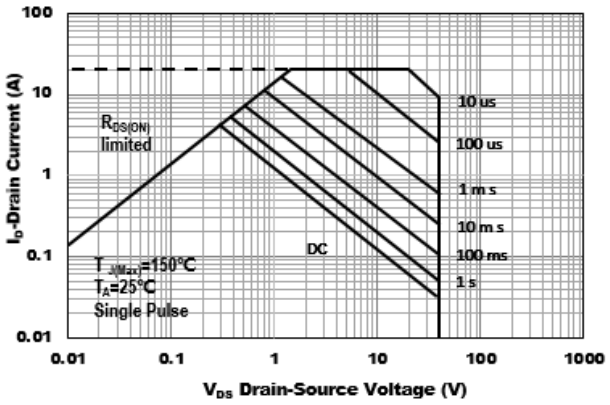


Figure7. Safe Operation Area

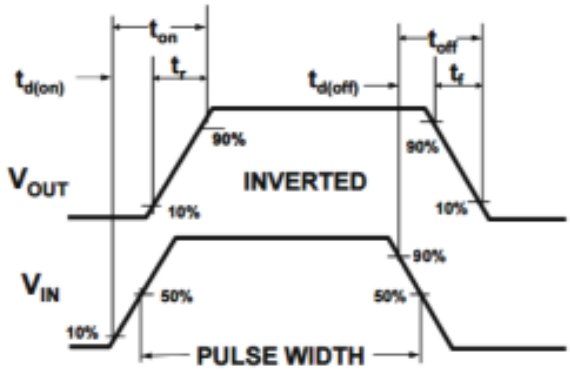
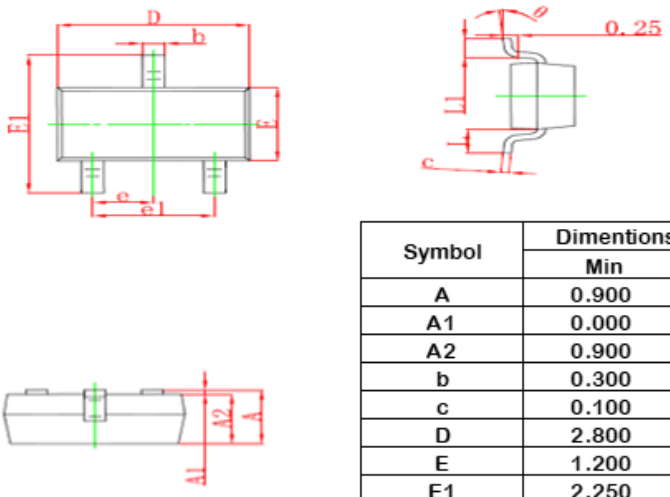


Figure8. Switching wave

SOT-23 Package information



Symbol	Dimentions in Millimeter		Dimentions in Inches	
	Min	Max	Min	Max
A	0.900	1.150	0.035	0.045
A1	0.000	0.100	0.000	0.004
A2	0.900	1.050	0.035	0.041
b	0.300	0.500	0.012	0.020
c	0.100	0.200	0.004	0.008
D	2.800	3.000	0.110	0.118
E	1.200	1.400	0.047	0.055
E1	2.250	2.550	0.089	0.100
e	0.950Type		0.037Type	
e1	1.800	2.000	0.071	0.079
L	0.550REF		0.220REF	
L1	0.300	0.500	0.012	0.020
θ	0 °	8 °	0 °	8 °

SOT-23 Suggested Pad Layout